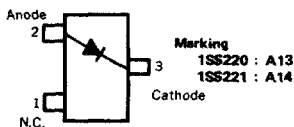
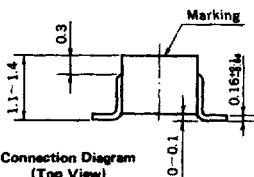
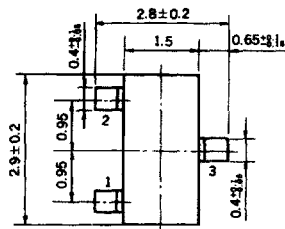


SILICON SWITCHING DIODES

1SS220, 1SS221

HIGH SPEED SWITCHING SILICON EPITAXIAL DIODES MINI MOLD

PACKAGE DIMENSIONS
in millimeters



FEATURES

- Low capacitance: $C_i = 4.0 \text{ pF MAX.}$
- High speed switching: $t_{rr} = 3.0 \text{ ns MAX.}$
- Wide applications including switching, limiter, clipper.

ABSOLUTE MAXIMUM RATINGS

Maximum Voltages and Currents ($T_a = 25^\circ\text{C}$)

		1SS220	1SS221	
Peak Reverse Voltage	V_{RM}	70	100	V
DC Reverse Voltage	V_R	70	100	V
Peak Forward Current	I_{FM}	300	300	mA
Average Rectified Current	I_O	100	100	mA
DC Forward Current	I_F	100	100	mA

Maximum Temperatures

Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{std}	-55 to +150	°C

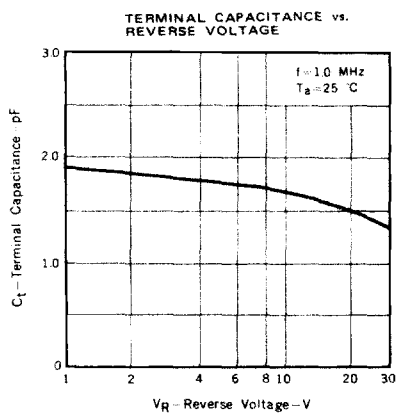
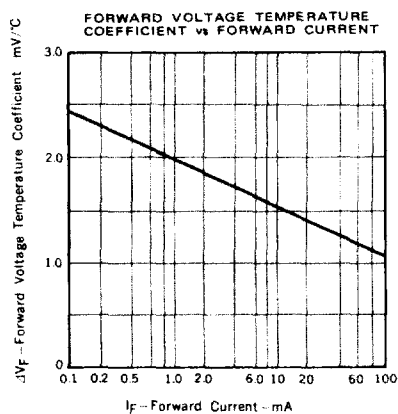
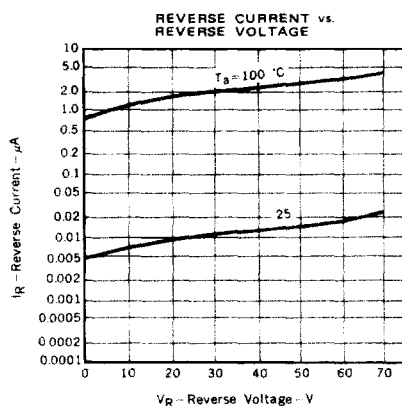
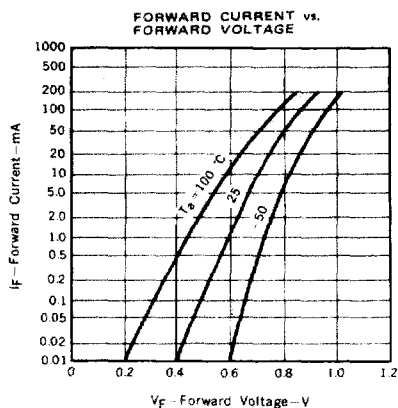
Thermal Resistance

Junction to Ambient	$R_{th(j-a)}$	0.67	$^{\circ}\text{C}/\text{mW}$
---------------------	---------------	------	------------------------------

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

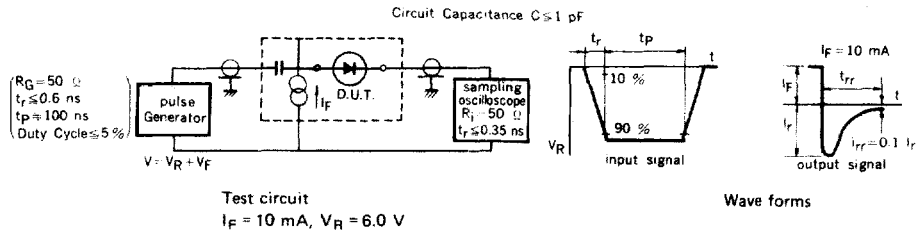
CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Forward Voltage	V_{F1}		720	850	mV	$I_F = 10 \text{ mA}$
	V_{F2}		850	1000	mV	$I_F = 50 \text{ mA}$
	V_{F3}		950	1200	mV	$I_F = 100 \text{ mA}$
Reverse Current	I_R	1SS220		1.0	μA	$V_R = 70 \text{ V}$
		1SS221		1.0	μA	$V_R = 100 \text{ V}$
Capacitance	C_t		2.0	4.0	pF	$V_R = 0, f = 1.0 \text{ MHz}$
Reverse Recovery Time	t_{rr}			3.0	ns	$I_F = 10 \text{ mA}, V_R = 6 \text{ V},$ $R_L = 100 \Omega, \text{ See Test Circuit.}$

NEC cannot assume any responsibility for any circuits shown or represent that they are free from patent infringement.

TYPICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

SWITCHING CHARACTERISTICS TEST CIRCUIT

Reverse recovery time : t_{rr}



DC-1056A
March 1991 M
Printed in Japan